

# STTB306B(-TR)

# TURBOSWITCH™ "B" . ULTRA-FAST HIGH VOLTAGE DIODE

#### MAIN PRODUCT CHARACTERISTICS

I <sub>F(AV)</sub>	3 A
V <sub>RRM</sub>	600 V
<b>V</b> F (max)	1.3 V
t <sub>rr</sub> (typ)	45 ns

#### FEATURES AND BENEFITS

- SPECIFIC TO THE FOLLOWING OPERATIONS: SNUBBING OR CLAMPING, DEMAGNETIZA-TION AND RECTIFICATION
- ULTRA-FAST, VERY SOFT AND NOISE-FREE RECOVERY
- VERY LOW OVERALL POWER LOSSES AND PARTICULARY LOW FORWARD VOLTAGE
- DESIGNED FOR HIGH PULSED CURRENT OP-ERATIONS
- SURFACE MOUNT DEVICE
- TAPE AND REEL OPTION : -TR

#### DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast voltage power diodes from 600V to 1200V.

TURBOSWITCH "B" family drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes. They are particulary suitable in the primary circuit

#### **ABSOLUTE MAXIMUM RATINGS**



of an SMPS as snubber, clamping or demagnetizer diodes, and also in most power converters as high performance Rectifier diodes.

Packaged in DPAK Surface Mount enveloppe, these 600V devices are particulary intended for use on 240V domestic mains.

Symbol	Parameter	Value	Unit	
Vrrm	Repetitive Peak Reverse Voltage	600	V	
V <sub>RSM</sub>	Non Repetitive Surge Reverse Voltage	600	V	
I <sub>F(RMS)</sub>	RMS Forward Current	8	А	
I <sub>FRM</sub>	Repetitive Peak Forward Current	tp = 5 μs F = 1 KHz	110	A
T <sub>stg</sub>	Storage Temperature Range	- 65 to + 150	°C	
Tj	Max. Junction Temperature	125	°C	

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# THERMAL AND POWER DATA

Symbol	Parameter	Conditions	Value	Unit
R <sub>th (j-c)</sub>	Junction to Case Thermal Resistance	TBD	°C/W	
P <sub>1</sub>	Conduction Power Dissipation	$I_{F(AV)} = 1.5A, \delta = 0.5$ $T_L = °C$	TBD	W
P <sub>max</sub>	Total Power Dissipation $P_{max} = P_1 + P_3$ (P <sub>3</sub> = 10% P <sub>1</sub> )	T <sub>L</sub> = 76°C	TBD	°C/W

## STATIC ELECTRICAL CHARACTERISTICS

Symbol	<b>Tests Conditions</b>	Tests	Min.	Тур.	Max.	Unit	
I <sub>R</sub> *	Reverse leakage	Tj = 25°C	$V_R = 0.8 \text{ X} V_{RRM}$			20	μA
	Current	Tj = 125°C				500	μA
VF **	Forward Voltage drop	Tj = 25°C	I <sub>F</sub> = 3 A			1.4	V
		Tj = 125°C	I <sub>F</sub> = 3 A			1.3	

Pulse test : \* tp = 5 ms, duty cycle < 2 %

tp = 5 ms, duty cycle < 2 % \*\* tp = 380  $\mu$ s, duty cycle < 2%

## DYNAMIC ELECTRICAL CHARACTERISTICS

#### **TURN-OFF SWITCHING**

Symbol	Parameter	Test Conditions			Тур.	Max.	Unit
t <sub>rr</sub>		Tj = 25℃	I <sub>F</sub> =0.5A I <sub>R</sub> =1A I <sub>rr</sub> =0.25A I <sub>F</sub> =1A dI <sub>F</sub> /dt=A/μs V <sub>R</sub> =30V		45	95	ns
t <sub>fr</sub>	Maximum Reverse Recovery Current	Tj = 125℃	I <sub>F</sub> =2A V <sub>R</sub> =400V dI <sub>F</sub> /dt = -16A/μs dI <sub>F</sub> /dt = -50A/μs		3.6	2.4	A
S factor	Softness Factor	Tj = 125℃	V <sub>R</sub> =400V I <sub>F</sub> =2A dI <sub>F</sub> /dt = -50A/μs		TBD		/

# **TURN-ON SWITCHING**

Symbol	Parameter	Test Conditions			Тур.	Max.	Unit
t <sub>rr</sub>	Forward Recovery Time	Tj = 25℃	$I_F=2A$ $dI_F/dt = 16A/\mu s$ Measured at 1.1 x $V_{Fmax}$			500	ns
Vpf	Peak Forward	Tj = 25℃	I <sub>F</sub> =2A dI <sub>F</sub> /dt = 16A/μs			8	V
	Voltage	T j= 25℃	I <sub>F</sub> =5A dI <sub>F</sub> /dt = 50A/μs		6		



#### PACKAGE MECHANICAL DATA DPAK



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